

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

|  |                 |                  |
|--|-----------------|------------------|
| ATTY. DOCKET NO.<br><b>200208506-1</b> | APPLICATION NO. | CONFIRMATION NO. |
| APPLICANT                              |                 |                  |
| <b>Kenneth K. Smith et al.</b>         |                 |                  |
| FILING DATE<br><b>herewith</b>         |                 | GROUP            |

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | PUBLICATION DATE | NAME           | Pages, Columns, Lines Where Relevant Passages or Figures Appear |
|------------------|-----------------|------------------|----------------|---|
| CP               | 1A 6,169,686B1  | Jan. 2, 2001     | Brug et al.    |   |
| CP               | 1B 6,259,644B1  | Jul. 10, 2001    | Tran et al.    |   |
| CP               | 1C 6,567,297 B2 | May 20, 2003     | R. Jacob Baker |   |
| CP               | 1D 2002/0101758 | Aug. 1, 2002     | R. Jacob Baker |   |
| CP               | 1E 2003/0039162 | Feb. 27, 2003    | R. Jacob Baker |   |
|                  | 1F              |                  |                |   |
|                  | 1G              |                  |                |   |
|                  | 1H              |                  |                |   |
|                  | 1I              |                  |                |   |
|                  | 1J              |                  |                |   |
|                  | 1K              |                  |                |   |

## FOREIGN PATENT DOCUMENTS

|  | DOCUMENT NUMBER | PUBLICATION DATE | NAME OF PATENTEE OR APPLICANT | Pages/Columns/Lines Where Relevant Passages/Figures Appear | Check if Translation attached |
|--|-----------------|------------------|-------------------------------|--|-------------------------------|
|  | 1L              |                  |                               |  |                               |
|  | 1M              |                  |                               |  |                               |
|  | 1N              |                  |                               |  |                               |
|  | 1O              |                  |                               |  |                               |
|  | 1P              |                  |                               |  |                               |

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

|    |    |  |
|----|----|--|
| CP | 1Q | "Nonvolatile RAM based on Magnetic Tunnel Junction Elements" by M. Durlam et al. 2000 IEEE International Solid-State Circuits Conference 07803-5853-8/00, Motorola Labs, Physical Sciences   |
| CP | 1R | "A 10ns Read and Write Non-volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell" by Roy Scheuerlein et al. 2000 IEEE International Solid-State Circuits Conference 07803-5853-8/00, IBM Research Almaden Research Center, San Jose, CA, Section TA 7.2 |
| CP | 1S | "Offset Compensating Bit-Line Sensing Scheme for High Density DRAM's" by Yoshi Watanabe et al. IEE Jurnal of Solid-State Circuits. Vol. 29, No. 1, January 1994.   |

EXAMINER

DATE CONSIDERED

11/8/04